orm PTO 1449		U.S. DEPARTMENT OF COMMERCE		ATTY DOCKET NO.		SERIAL NO. 10/63/1		
odified) PATENT AND TRADEMARK OFFICE			241098US2SRD		NEW APPLICATION			
			APPLICANT					
LIST OF REFERENCES CITED BY APPLICANT				Mizuki ONO, et al.				
			FILING DATE		GROUP O CA			
			HEREWITH		0815			
				U.S. PATENT DOCUMENTS				
XAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
, 00 000	-AA						,	
	AB		<u> </u>					
	AC		<u> </u>					
	AD		<u> </u>				· · · · · · · · · · · · · · · · · · ·	
	AE							
	AF							
	AG		J					
	AH							
	Al		<u> </u>					
	AJ		ļ					
 	AK		_					
	AL							
	AM					ļ		
	AN	L	<u> </u>					
			FC	REIGN PATENT DOCUME	ITS			
		DOCUMENT NUMBER	DATE	COUNTRY		TRANSLATION YES NO		
50	AO	2002-16063	01/18/02	Japan			×	
<i>3</i> n)	AP	2000-307010	11/02/02	Japan			×	
	AQ							
	AR			<u> </u>				
	AS					<u> </u>		
	AT					ļ		
	AU	ļ			·	 		
	AV			<u> </u>				
				(Including Author, Title, Da				
570)	AW	G. LUCOVSKY, et all Zr and Hf Silicate All	., "Microscopic bys", APPLIED	Model for Enhanced Dielectr PHYSICS LETTERS, Vol. 7	c Constants in Low Co 7, No. 18, October 30,	ncentratio 2000, pgs.	n SiO ₂ -Rich Noncrystallin 2912-2914	
Th	AX	Angus I. KINGON, et al., "Alternative Dielectrics to Silicon Dioxide for Memory and Logic Devices", NATURE, Vol. 406, August 31, 2000, pgs. 1032-1038						
	AY							
	AZ				Add	litional Refe	erences sheet(s) attached	
	.1						125-41	
examiner SD						Date Considered 6-25-04		